

<Transistor>

# 2SC5626

For High Frequency Amplify Application  
Silicon NPN Epitaxial Type (Super Mini type)

## DESCRIPTION

Mitsubishi 2SC5626 is a super mini package resin sealed silicon NPN epitaxial type transistor. It is designed for high frequency amplify application.

## FEATURE

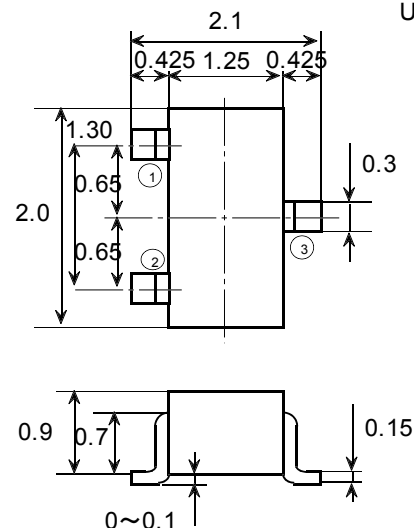
- Super mini package for easy mounting
- High gain band width product

## APPLICATION

Small type machine high frequency amplify application

## OUTLINE DRAWING

Unit:mm



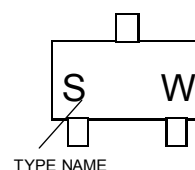
## TERMINAL CONNECTOR

- ① : BASE  
② : EMITTER  
③ : COLLECTOR
- JEITA : SC-70  
JEDEC : -

## MAXIMUM RATINGS (Ta=25°C)

SYMBOL	PARAMETER	RATINGS	UNIT
V <sub>CB0</sub>	Collector to Base voltage	30	V
V <sub>EB0</sub>	Emitter to Base voltage	4	V
V <sub>CEO</sub>	Collector to Emitter voltage	20	V
I <sub>C</sub>	Collector current	50	mA
P <sub>C</sub>	Collector dissipation(Ta=25°C)	150	mW
T <sub>j</sub>	Junction temperature	+150	°C
T <sub>stg</sub>	Storage temperature	-55to+150	°C

## MARKING



## ELECTRICAL CHARACTERISTICS (Ta=25°C)

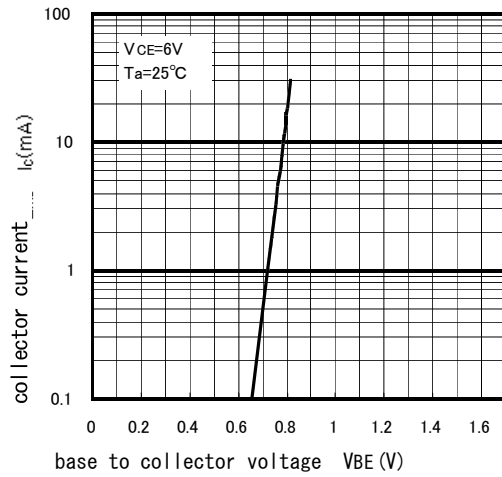
SYMBOL	PARAMETER	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
V <sub>(BR)CBO</sub>	C to B break down voltage	I <sub>C</sub> =50 μA, I <sub>E</sub> =0mA	30			V
V <sub>(BR)CEO</sub>	C to E break down voltage	I <sub>C</sub> =100 μA, R <sub>BE</sub> =∞	20			V
V <sub>(BR)EBO</sub>	E to B break down voltage	I <sub>C</sub> =50 μA, I <sub>C</sub> =0mA	4			V
I <sub>CB0</sub>	Collector cut off current	V <sub>CB</sub> =20V, I <sub>E</sub> =0			0.5	μA
I <sub>EB0</sub>	Emitter cut off current	V <sub>EB</sub> =3V, I <sub>C</sub> =0			0.5	μA
h <sub>FE</sub>	DC forward current gain	V <sub>CE</sub> =10V, I <sub>C</sub> =5mA	50	148		—
V <sub>CE(sat)</sub>	C to E Saturation voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.1	0.3	V
f <sub>T</sub>	Gain band width product	V <sub>CE</sub> =5V, I <sub>E</sub> =-10mA	600	1100		MHz
C <sub>ob</sub>	Collector output capacitance	V <sub>CB</sub> =6V, I <sub>E</sub> =0, f=1MHz		1.2	1.5	pF

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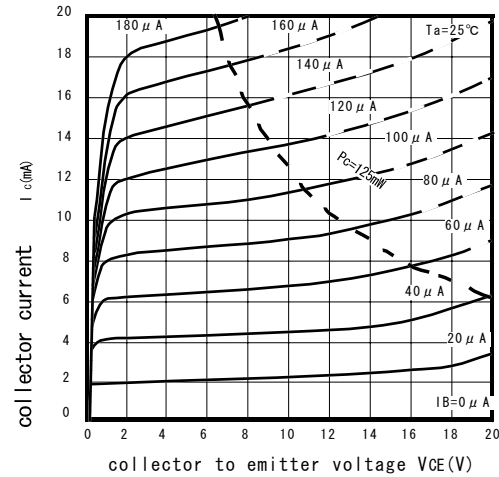
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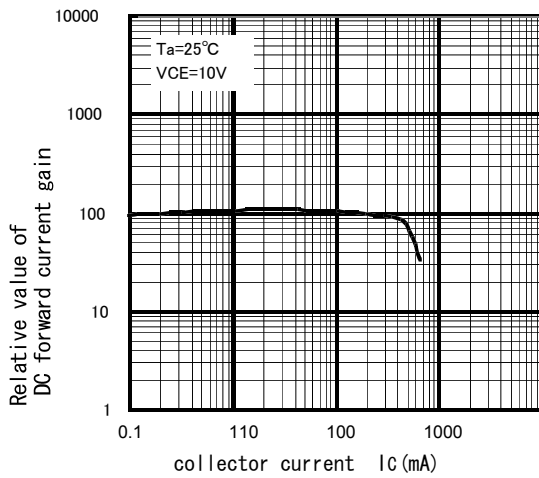
Common emitter output



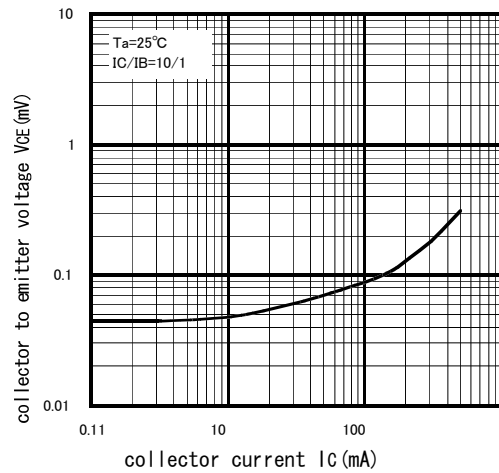
Common emitter transfer



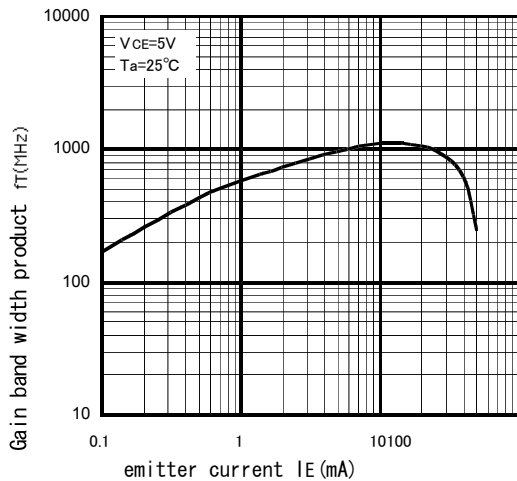
DC forward current gain VS. collector current



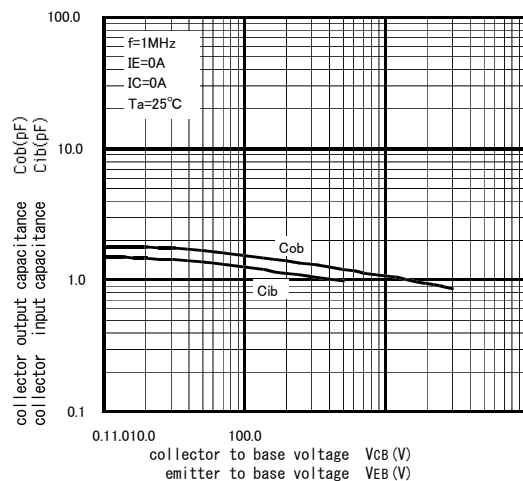
collector to emitter voltage VS. collector current



Gain band width product VS. Emitter current



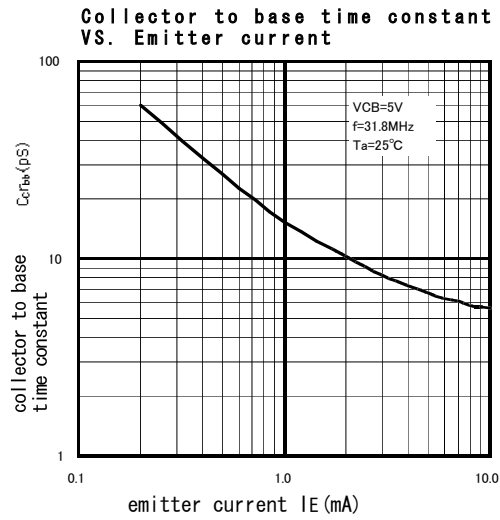
collector output/input capacitance VS. Collector to Base Voltage



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